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Kind regards,

Team Nexperia



PBSS5230T

30 V, 2 A PNP low VCEsat (BISS) transistor Rev. 2 — 4 June 2012

Product data sheet

1. **Product profile**

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4230T.

1.2 Features and benefits

- Low collector-emiter saturation voltage
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- AEC-Q101 qualified

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting

- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -500 mA; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	160	220	Ω



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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	Е	emitter		3
3	С	collector	1 2	1—
			SOT23 (TO-236AB)	2 sym013

3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5230T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS5230T	%3G

^{[1] % =} placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-30	V
V_{CEO}	collector-emitter voltage	open base		-	-30	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-3	Α
I _B	base current			-	-300	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T_{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

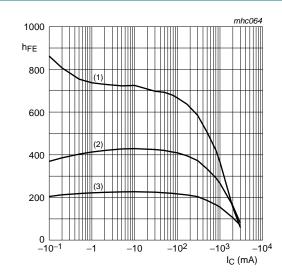
7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; T_{amb} = 25 °C	300	450	-	
		$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	200	290	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	100	180	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}$; $I_B = -50 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	-	-70	-110	mV
		$I_C = -1 \text{ A}$; $I_B = -50 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	-	-140	-225	mV
		I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	-	-240	-350	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}; \text{ pulsed}; \\ t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$	-	160	220	Ω
V _{BEsat}	base-emitter saturation voltage	I_{C} = -2 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	-0.75	V
f _T	transition frequency	$V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$ f = 100 MHz; $T_{amb} = 25 \text{ °C}$	100	200	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	23	28	pF

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

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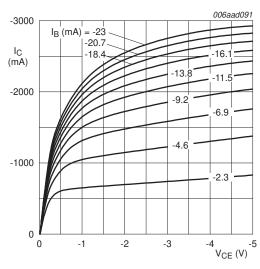
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

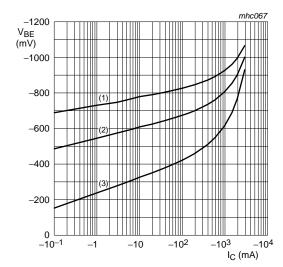
(3)
$$T_{amb} = -55$$
 °C

Fig 1. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 2. Collector current as a function of collector-emitter voltage; typical values



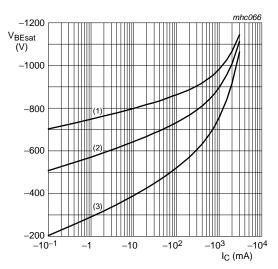
 $V_{CE} = -2 V$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 3. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

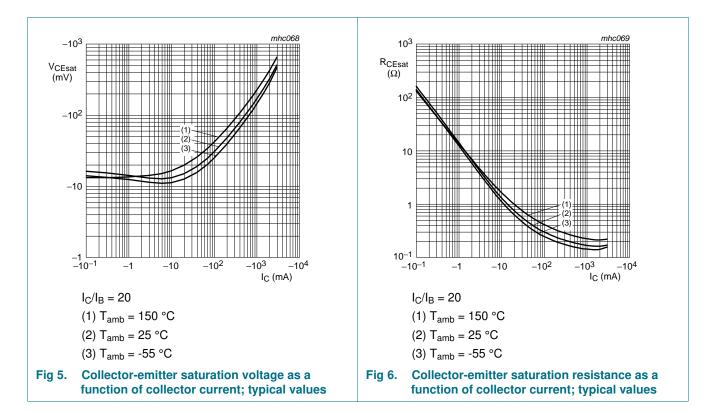
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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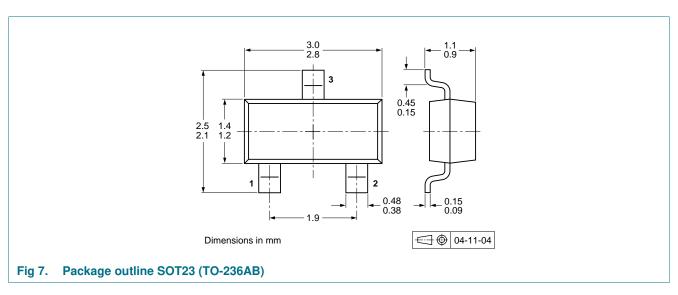


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



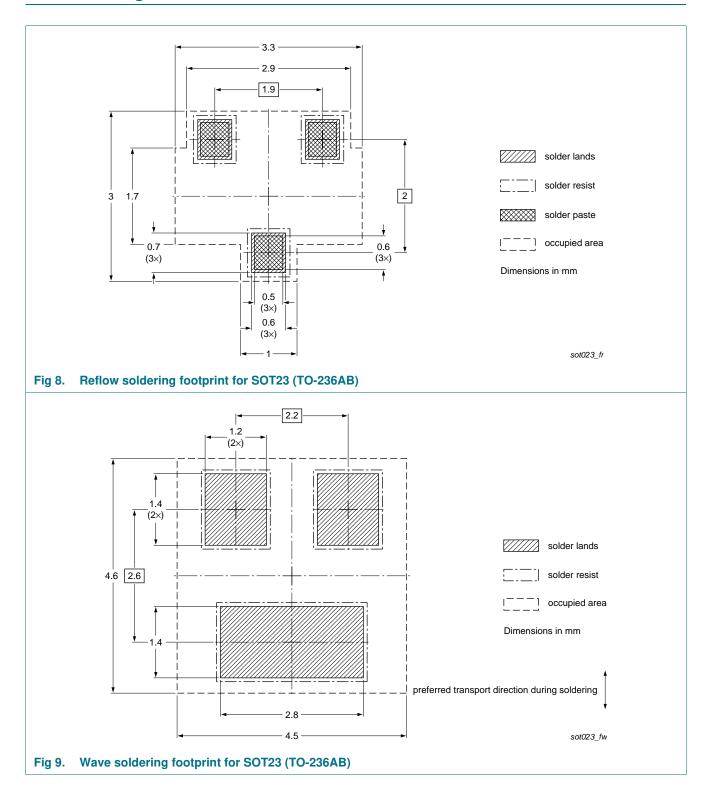
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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5230T v.2	20120604	Product data sheet	-	PBSS5230T v.1		
Modifications:	 The format of this document has been redesigned to comply with the new identity guide NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	<u>1 "Product profile"</u> : updated					
	• <u>Table 5.</u> : updated					
	 <u>7 "Characteristics"</u>: V_{CEsat} corrected, <u>Fig 1.</u> to <u>Fig 6.</u> added 					
	8 "Test information	<u>ı"</u> : added				
 9 "Package outline": replaced by minimized package outline drawing 						
	• 10 "Soldering": add	ded				
PBSS5230T v.1	20031218	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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